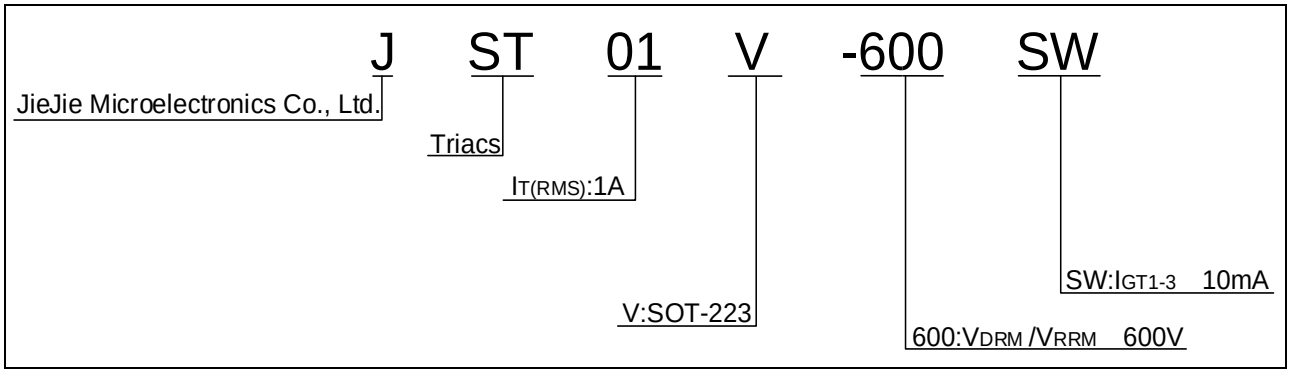
**JST01V-8C6 m 8837 (**

SJS01V -

Peak pulse voltage
($T_j$ -

## ORDERING INFORMATION




## MARKING

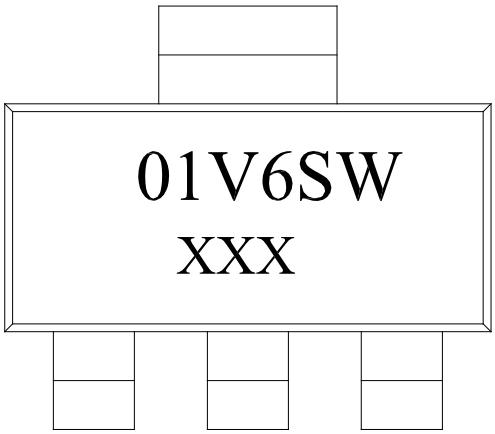


**FIG.1:** Maximum power dissipation versus RMS

**FIG.7:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

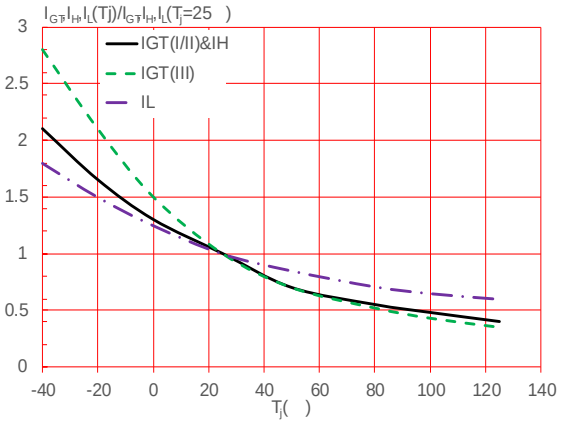
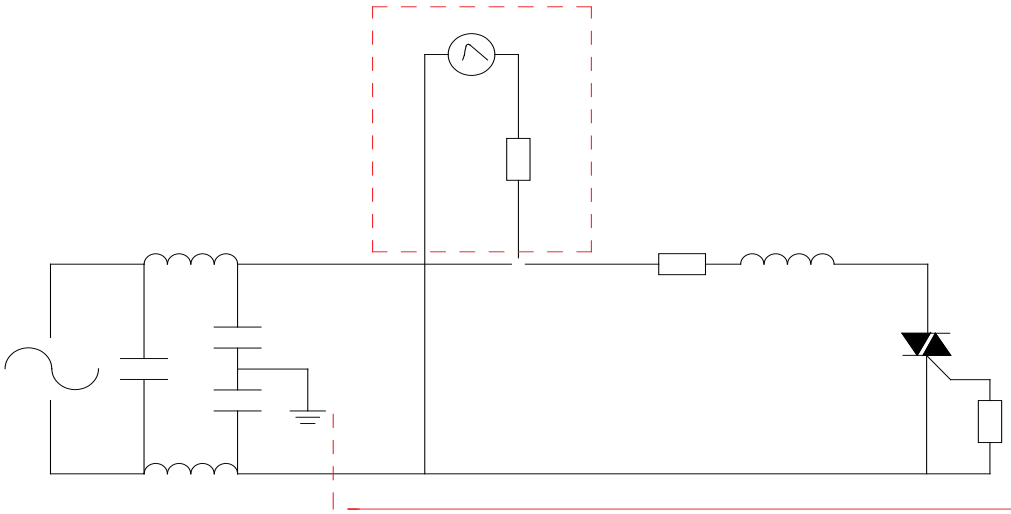


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



**JST01V-**

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